IXYS

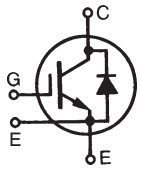
Preliminary Technical Information

1200V XPT™ IGBT GenX3™ w/ Diode

IXYN100N120B3H1

V_{CES} = 1200V
I_{C110} = 76A
$V_{CE(sat)}$ ≤ 2.6V
$t_{fi(typ)}$ = 240ns

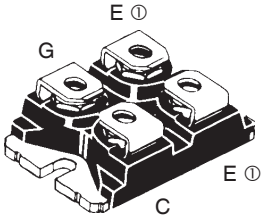
Extreme Light Punch Through
IGBT for 5-30 kHz Switching



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	1200	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ	1200	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C (Chip Capability)	165	A
I_{C110}	T_C = 110°C	76	A
I_{F110}	T_C = 110°C	42	A
I_{CM}	T_C = 25°C, 1ms	480	A
I_A	T_C = 25°C	50	A
E_{AS}	T_C = 25°C	1.2	J
SSOA (RBSOA)	V_{GE} = 15V, T_{VJ} = 150°C, R_G = 1Ω Clamped Inductive Load	I_{CM} = 200 @$V_{CE} \leq V_{CES}$	A
P_C	T_C = 25°C	690	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
V_{ISOL}	50/60Hz t = 1min $I_{ISOL} \leq$ 1mA t = 1s	2500 3000	V~ V~
M_d	Mounting Torque Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in. Nm/lb.in.
Weight		30	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V	1200			V
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}	3.0		5.0	V
I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0V			50	μA
	T_J = 125°C			2.75	mA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±100	nA
$V_{CE(sat)}$	I_C = 100A, V_{GE} = 15V, Note 1		2.20	2.60	V
	T_J = 150°C		2.76		V

SOT-227B, miniBLOC
E153432



G = Gate, C = Collector, E = Emitter
① either emitter terminal can be used as Main or Kelvin Emitter

Features

- Optimized for 5-30kHZ Switching
- Square RBSOA
- 2500V~ Isolation Voltage
- Anti-Parallel Ultra Fast Diode
- Positive Thermal Coefficient of Vce(sat)
- Avalanche Rated
- High Current Handling Capability
- International Standard Package

Advantages

- High Power Density
- Low Gate Drive Requirement

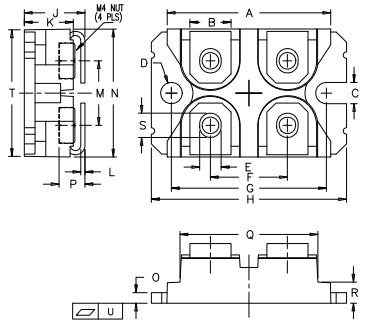
Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

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Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 60A, V_{CE} = 10V, Note 1	30	52		S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		6000		pF
C_{oes}			367		pF
C_{res}			127		pF
$Q_{g(on)}$	I_C = 100A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		250		nC
Q_{ge}			42		nC
Q_{gc}			96		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		30		ns
t_{ri}	I_C = 100A, V_{GE} = 15V		90		ns
E_{on}	V_{CE} = 0.5 • V_{CES}, R_G = 1Ω		7.7		mJ
$t_{d(off)}$	Note 2		153		ns
t_{fi}			240		ns
E_{off}			7.1	11.5	mJ
$t_{d(on)}$	**Inductive load, T_J = 150°C**		29		ns
t_{ri}	I_C = 100A, V_{GE} = 15V		96		ns
E_{on}	V_{CE} = 0.5 • V_{CES}, R_G = 1Ω		11.4		mJ
$t_{d(off)}$	Note 2		190		ns
t_{fi}			260		ns
E_{off}			10.1		mJ
R_{thJC}				0.18	°C/W
R_{thCS}			0.05		°C/W

SOT-227B miniBLOC (IXYN)



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

Reverse Diode (FRED)

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
V_F	I_F = 60A, V_{GE} = 0V, Note 1			2.7	V
	T_J = 125°C		1.9		V
I_{RM}	I_F = 60A, V_{GE} = 0V, T_J = 125°C		41		A
t_{rr}	$-di_F/dt$ = 700A/μs, V_R = 600V		420		ns
R_{thJC}				0.42	°C/W

Notes:

1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

PRELIMANARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

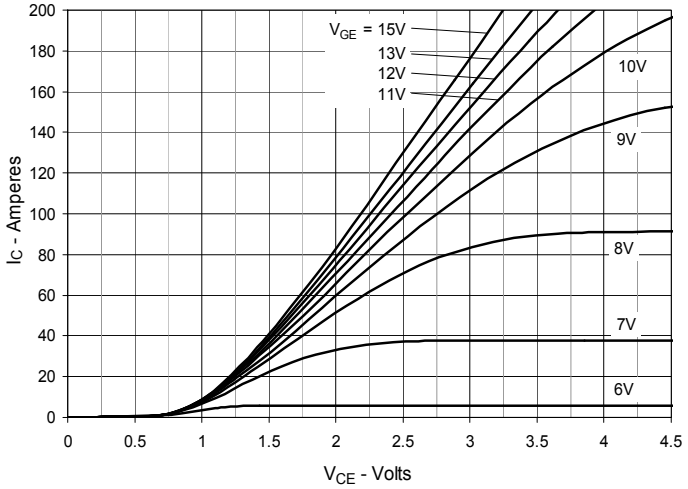


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

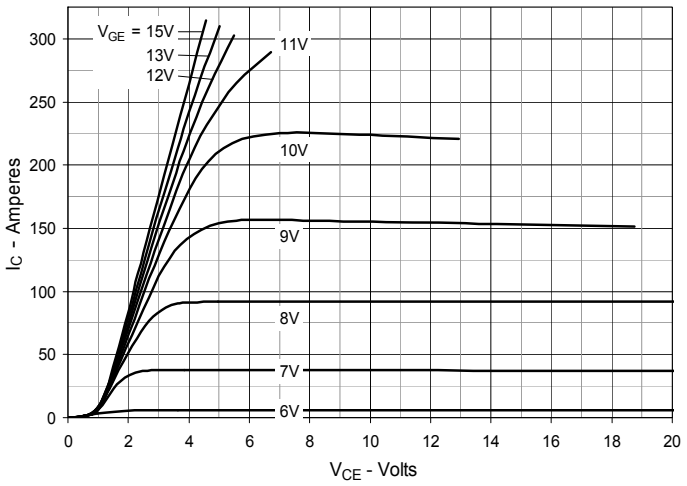


Fig. 3. Output Characteristics @ T_J = 150ºC

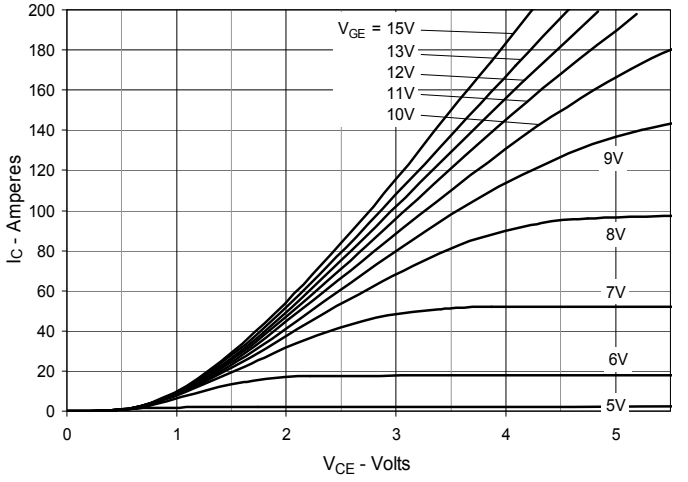


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

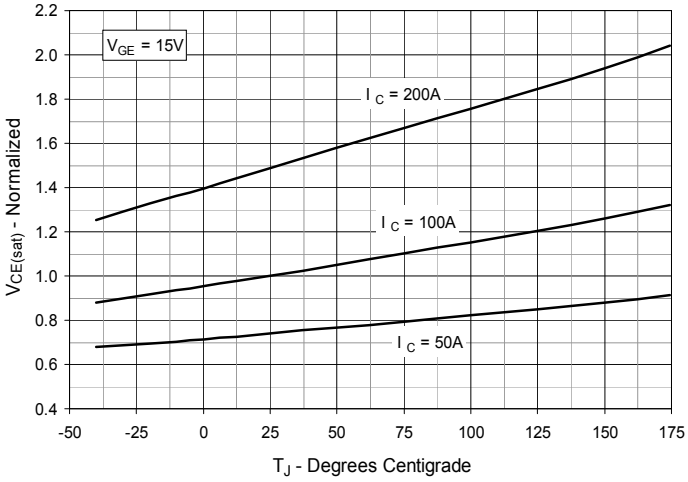


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

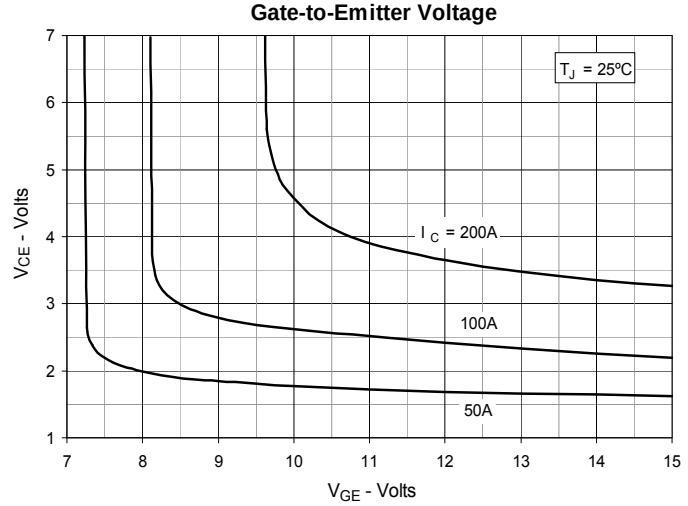
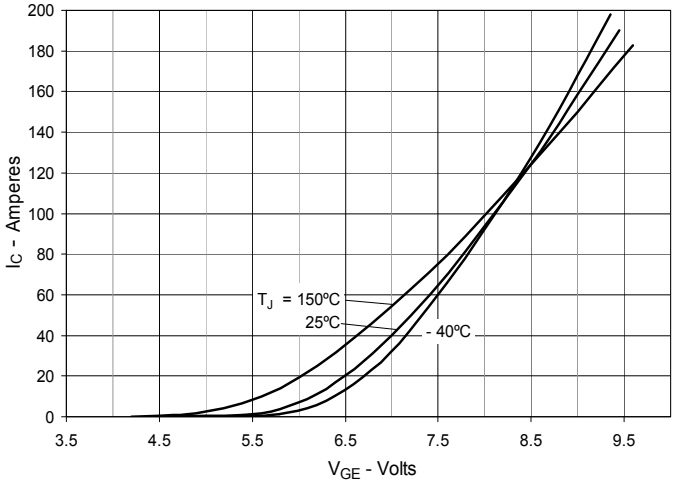


Fig. 6. Input Admittance



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Fig. 7. Transconductance

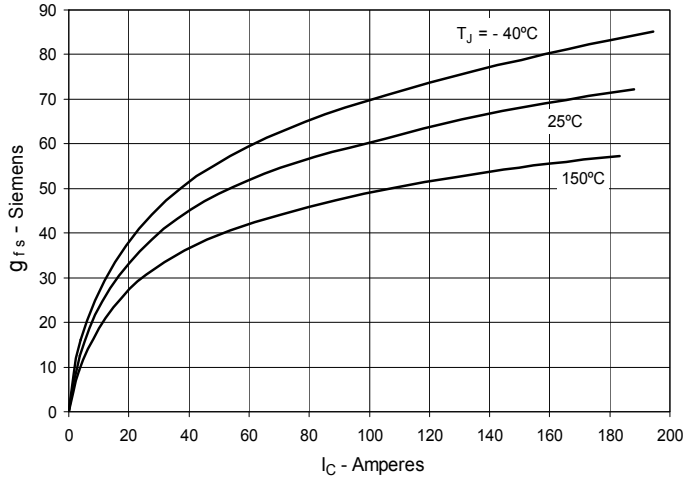


Fig. 8. Gate Charge

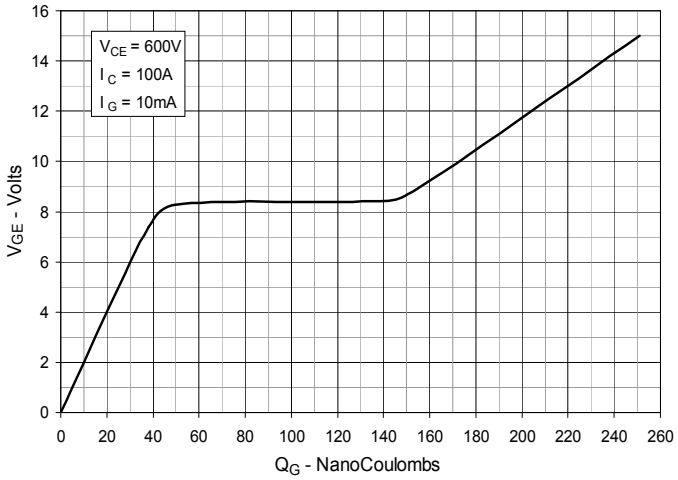


Fig. 9. Capacitance

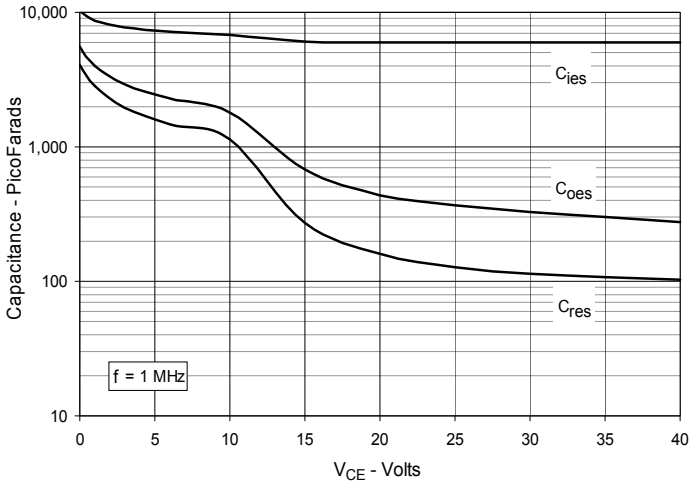


Fig. 10. Reverse-Bias Safe Operating Area

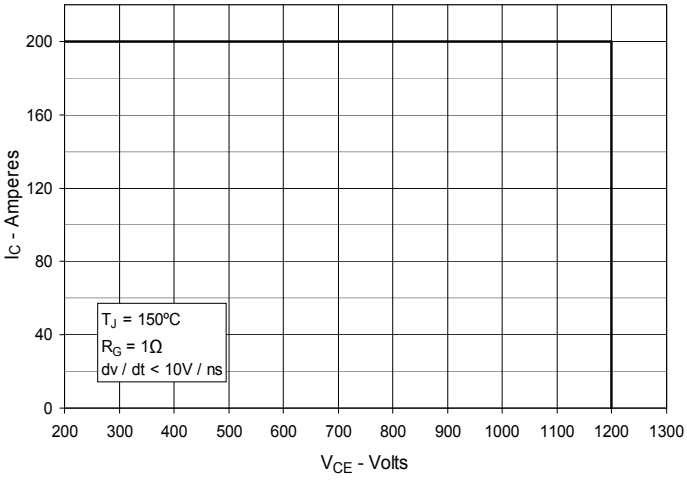
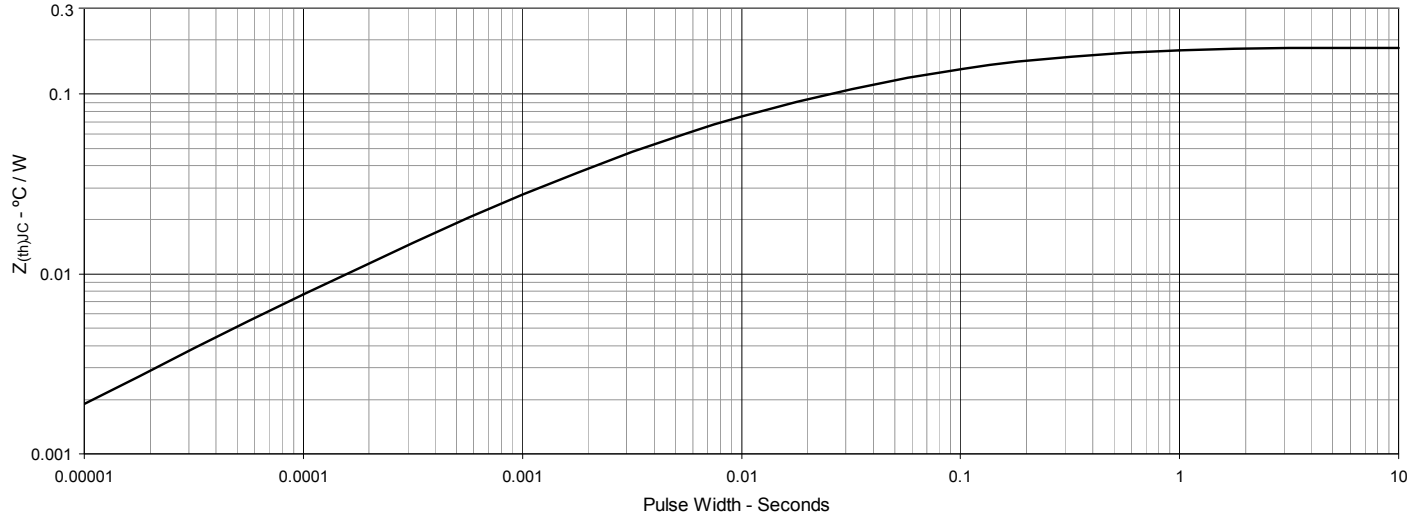


Fig. 11. Maximum Transient Thermal Impedance



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

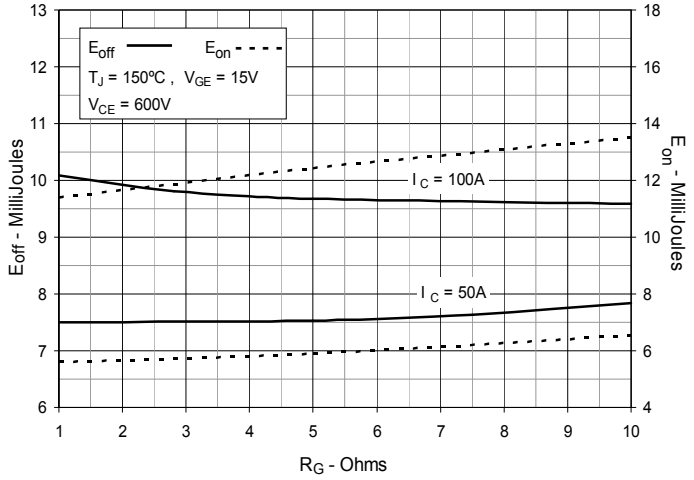


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

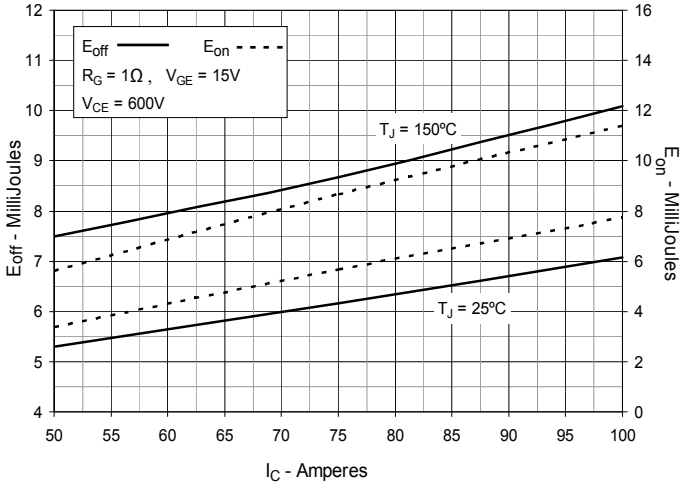


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

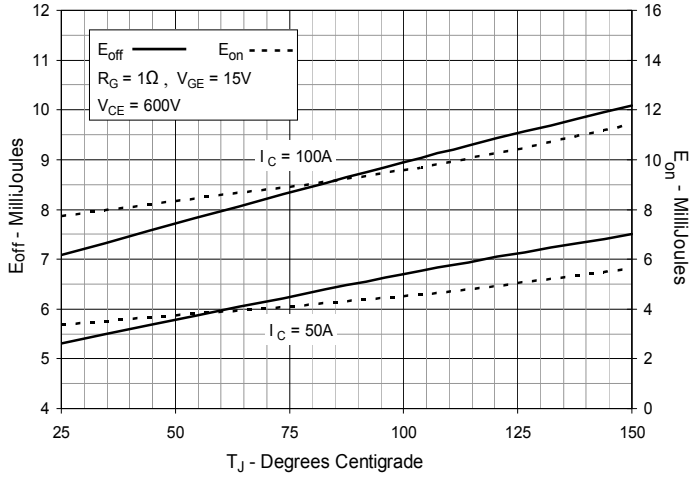


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

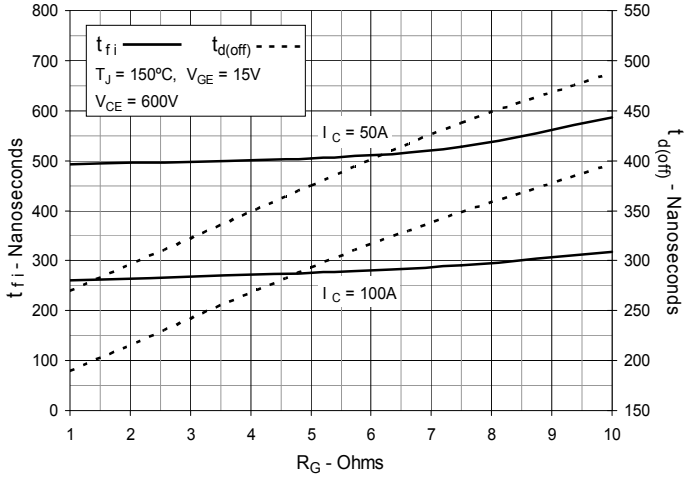


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

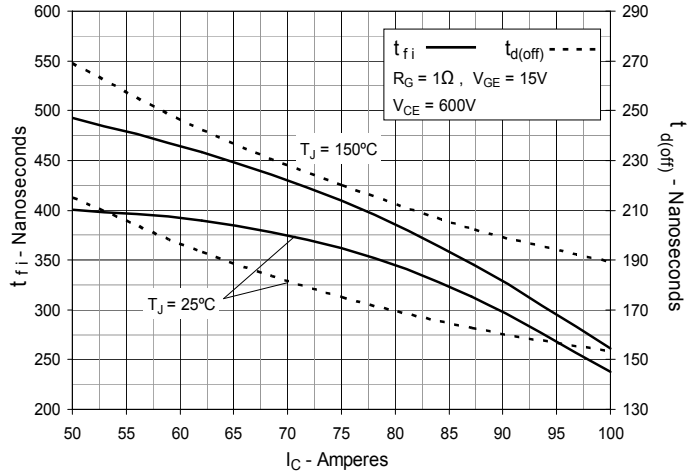
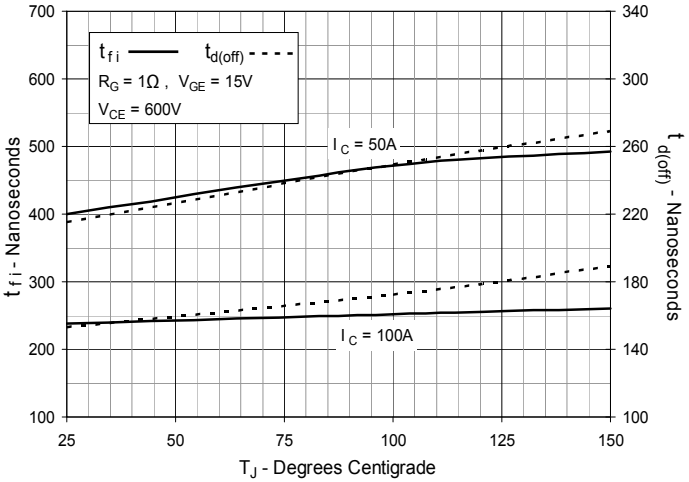


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature



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Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

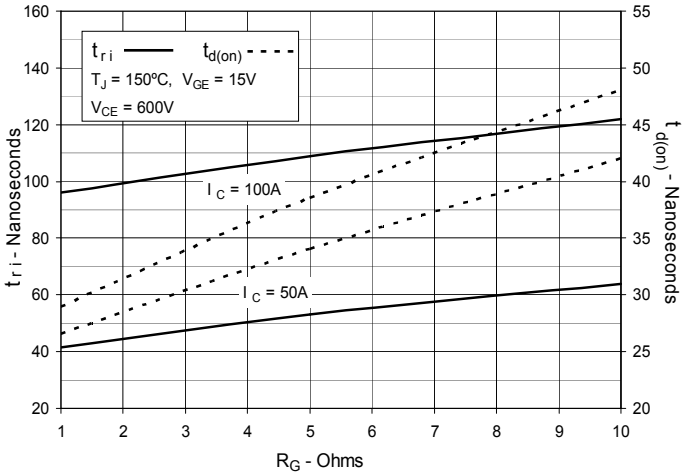


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

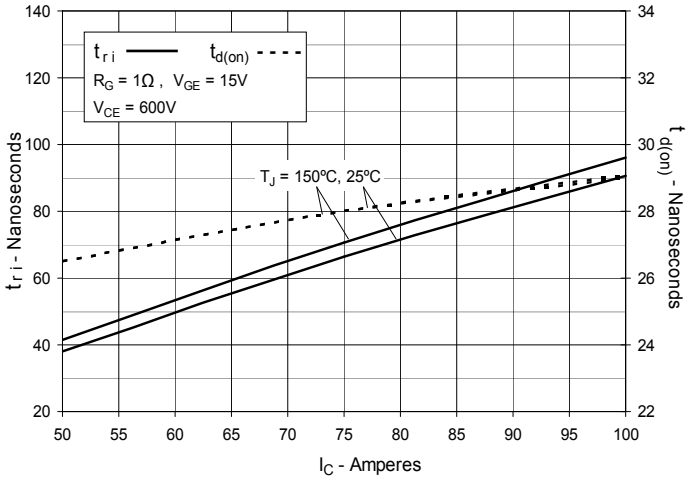


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

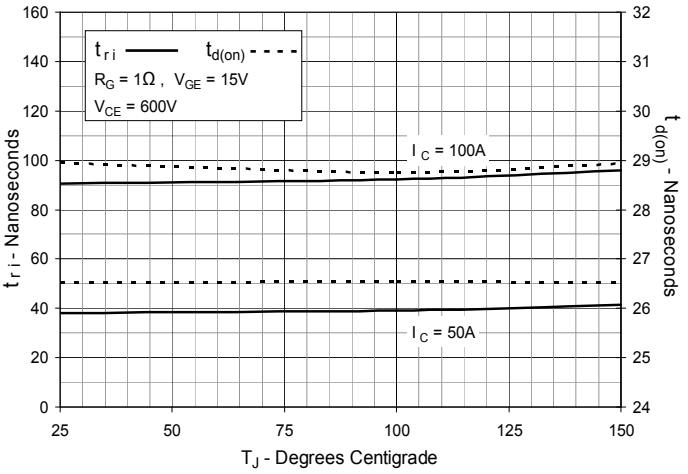


Fig. 21. Typ. Forward Characteristics

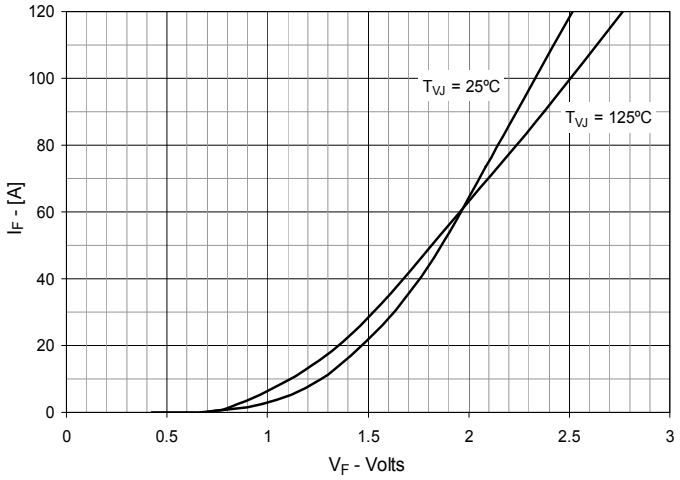


Fig. 22. Typ. Reverse Recovery Charge Q_{rr} vs. -di_F/dt

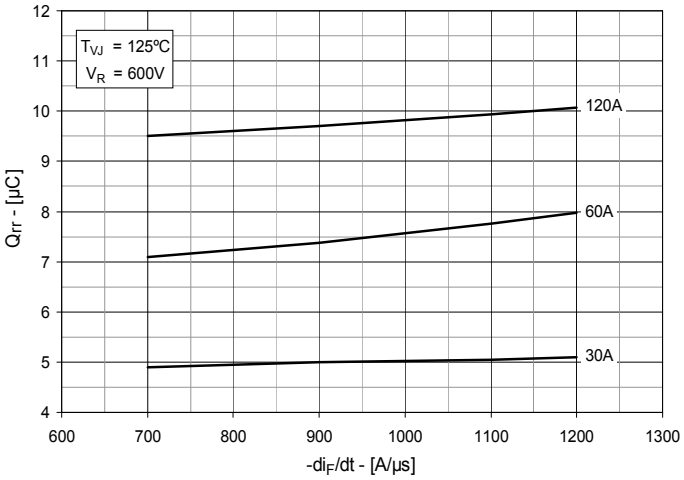


Fig. 23. Typ. PeakReverse Current I_{RM} vs. -di_F/dt

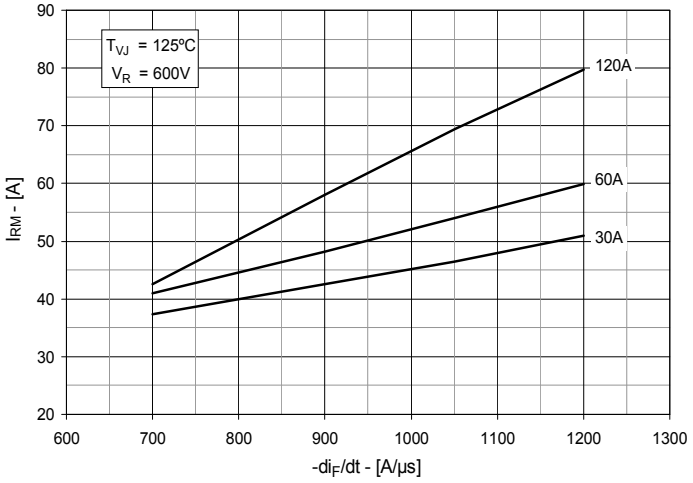


Fig. 24. Typ. Recovery Time t_{rr} vs. -di_F/dt

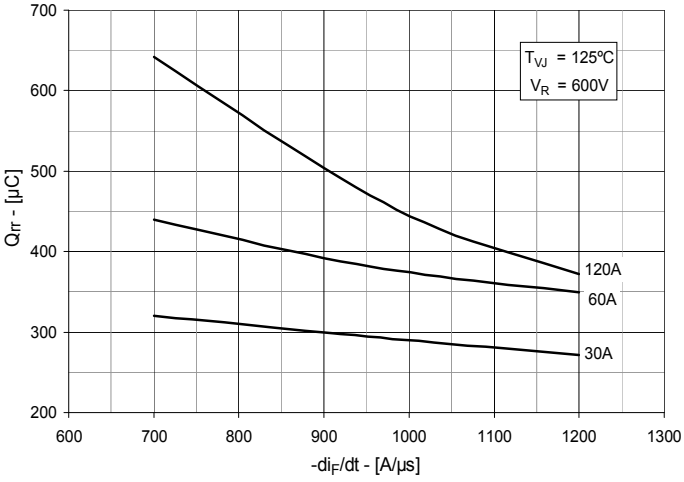


Fig. 25. Typ. Recovery Energy E_{rec} vs. -di_F/dt

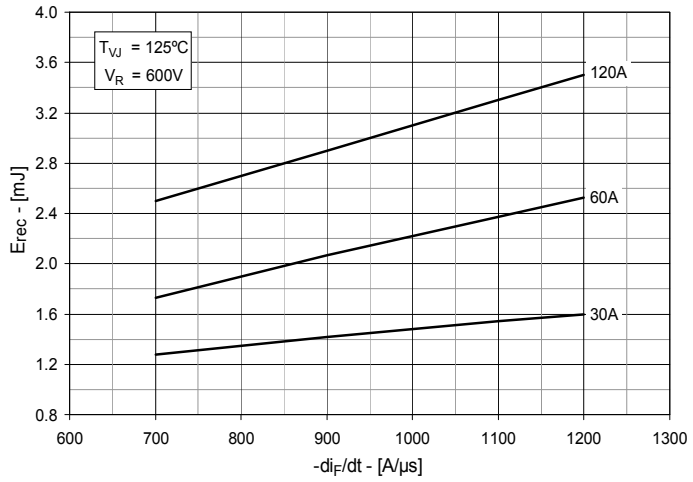
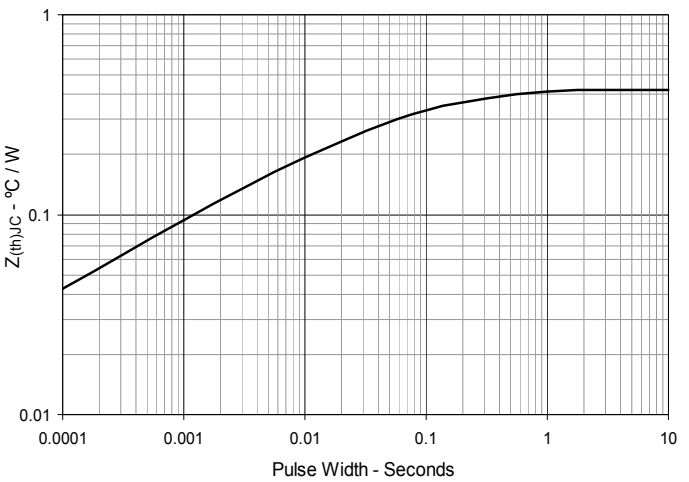


Fig. 26. Maximum Transient Thermal Impedance



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